HIGH CONDUCTANCE LOW LEAKAGE DIODES

T-01-09

1N3595
1N6099

ABSOLUTE MAXIMUM RATINGS

- B_v 150 V (MIN) @ 100 µA
- V_F 1.0 V @ 200 mA

Temperatures

Storage Temperature Range	-65 °C to +200 °C
Maximum Junction Operating Temperature	+175 °C
Lead Temperature	+260 °C

Power Dissipation

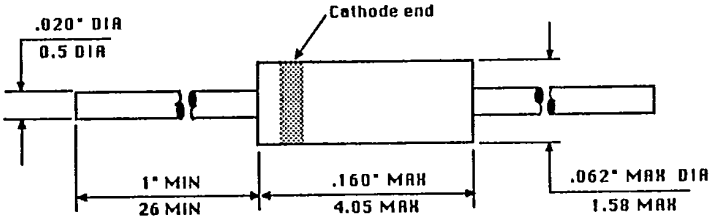
Maximum Total Power Dissipation at 25 °C Ambient	500 mW
Linear Power Derating Factor (from 25 °C)	3.33 mW/ °C

Maximum Voltage and Currents

WIV	Working Inverse Voltage	125 V
I_o	Average Rectified Current	200 mA
I_F	Forward Current Steady State	500 mA
i_F	Peak Repetitive Forward Current	600 mA
i_F (surge)	Peak Forward Surge Current	
	Pulse Width = 1.0 µs	4.0 A
	Pulse Width = 1.0 s	1.0 A

ELECTRICAL CHARACTERISTICS (25 °C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
V_F	Forward Voltage	0.83	1.0	V	I_F = 200 mA
		0.79	0.92	V	I_F = 100 mA
		0.75	0.88	V	I_F = 50 mA
		0.65	0.80	V	I_F = 10 mA
		0.60	0.75	V	I_F = 5.0 mA
		0.52	0.68	V	I_F = 1.0 mA
I_R	Reverse Current		1.0	nA	V_R = 125 V
			300	nA	V_R = 30 V, T_A = 125 °C
			500	nA	V_R = 125 V, T_A = 125 °C
			3.0	µA	V_R = 125 V, T_A = 150 °C
B_v	Breakdown Voltage	150		V	I_R = 100 µA
T_{RR}	Reverse Recovery Time		3.0	µs	I_F = 10 mA, V_R = 3.5 V, R_L = 1.0 kΩ
C	Capacitance		8.0	pF	V_R = 0, f = 1.0 MHz



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